

MiniSKiiP® 2

Converter-Inverter-Brake (CIB)

SKiiP 23NAB12T4V1

Features*

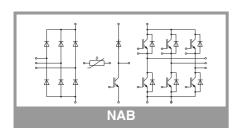
- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

Typical Applications

- Inverter up to 14 kVA
- Typical motor power 7,5 kW

- Max. case temperature limited to $T_C=125^{\circ}C$
- Product reliability results valid for T_j≤150°C (recommended T_{1:on}=-40...+150°C)
- T_{j,op}=-40...+150°C)
 MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information

Absolute	e Maximum Ratings	S		
Symbol	Conditions		Values	Unit
Inverter -	· IGBT			
V _{CES}	T _i = 25 °C		1200	V
Ic	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	37	Α
	T _j = 175 °C	T _s = 70 °C	30	Α
I _C	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	41	Α
	T _j = 175 °C	T _s = 70 °C	34	Α
I _{Cnom}			25	Α
I _{CRM}			75	Α
V _{GES}			-20 20	V
t _{psc}	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T _j = 150 °C	10	μѕ
Tj		•	-40 175	°C
Chopper	- IGBT			
V _{CES}	T _j = 25 °C		1200	V
Ic	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	37	А
	T _j = 175 °C	T _s = 70 °C	30	А
Ic	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	41	Α
	T _j = 175 °C	T _s = 70 °C	34	Α
I _{Cnom}			25	А
I _{CRM}			75	Α
V_{GES}			-20 20	V
t _{psc}	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T _j = 150 °C	10	μs
Tj			-40 175	°C
Inverse -	Diode		•	l e
V_{RRM}	T _i = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	32	Α
	T _j = 175 °C	T _s = 70 °C	26	Α
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	35	Α
	T _j = 175 °C	T _s = 70 °C	28	Α
I _{FRM}			75	А
I _{FSM}	$t_p = 10 \text{ ms, sin } 180^\circ$	°, T _j = 150 °C	100	Α
Tj	•	·	-40 175	°C
Freewhee	eling - Diode			l .
V _{RRM}	T _i = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	32	Α
	T _j = 175 °C	T _s = 70 °C	26	Α
I _F	λ_{paste} =2.5 W/(mK)	T _s = 25 °C	35	Α
	T _j = 175 °C	T _s = 70 °C	28	Α
I _{FRM}		1	75	Α
I _{FSM}	$t_p = 10 \text{ ms, sin } 180^\circ$	°, T _j = 150 °C	100	Α
Tj			-40 175	°C





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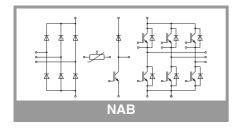
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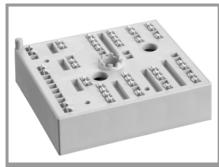
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Absolute Maximum Ratings								
Symbol	Conditions		Values	Unit				
Rectifier -	Diode			·				
V_{RRM}	T _j = 25 °C		1600	V				
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	52	Α				
	T _j = 150 °C	T _s = 70 °C	39	Α				
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	58	Α				
	T _j = 150 °C	T _s = 70 °C	44	Α				
I _{FSM}	t _p = 10 ms	T _j = 25 °C	370	Α				
	sin 180°	T _j = 150 °C	270	Α				
i ² t	$t_p = 10 \text{ ms}$	T _j = 25 °C	685	A ² s				
	sin 180°	T _j = 150 °C	365	A ² s				
T _j			-40 150 °					
Module								
I _{t(RMS)}	T _{terminal} = 80 °C, 20	A per spring	40	Α				
T _{stg}	module without TIN	Л	-40 125	°C				
V _{isol}	AC sinus 50 Hz, 1	min	2500	V				

Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
Inverter -	IGBT							
V _{CE(sat)}	$I_{\rm C} = 25 {\rm A}$	T _j = 25 °C		1.85	2.10	V		
	V _{GE} = 15 V chiplevel	T _j = 150 °C		2.25	2.45	٧		
V_{CE0}	chiplevel	T _j = 25 °C		0.80	0.90	V		
	Chipievei	T _j = 150 °C		0.70	0.80	V		
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		42	48	mΩ		
	chiplevel	T _j = 150 °C		62	66	mΩ		
$V_{\text{GE(th)}}$	$V_{GE} = V_{CE}$, $I_C = 1$ n	nĀ	5.3	5.8	6.3	V		
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = 12$	200 V, T _j = 25 °C			1	mA		
C _{ies}	V 05.V	f = 1 MHz		1.45		nF		
C _{oes}	$V_{CE} = 25 \text{ V}$ $V_{GF} = 0 \text{ V}$	f = 1 MHz		0.12		nF		
C _{res}	VGE - O V	f = 1 MHz	z 0.05			nF		
Q_{G}	V _{GE} = - 8 V+ 15 \	i I		142		nC		
R _{Gint}	T _j = 25 °C			0		Ω		
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		28		ns		
t _r	$I_C = 25 \text{ A}$ $R_{G \text{ on}} = 24 \Omega$	T _j = 150 °C		40		ns		
E _{on}	$R_{G \text{ off}} = 24 \Omega$	T _j = 150 °C	2.65		mJ			
t _{d(off)}	1 4 011 - 1 - 1	T _j = 150 °C	295			ns		
t _f		T _j = 150 °C		68				
E _{off}	V _{GE} = +15/-15 V	T _j = 150 °C	2.3			mJ		
R _{th(j-s)}	per IGBT, λ _{paste} =0.	8 W/(mK)		1.2		K/W		
$R_{th(j-s)}$	per IGBT, λ _{paste} =2.	5 W/(mK)		1		K/W		





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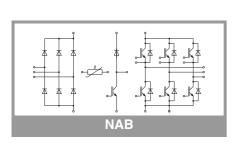
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- Highly reliable spring contacts for electrical connections
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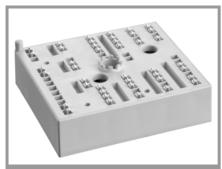
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- Max. case temperature limited to $T_C=125^{\circ}C$
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- T_{j,op}=-40...+150°C)
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Characte	eristics							
Symbol	Conditions		min.	typ.	max.	Unit		
Chopper				,.				
V _{CE(sat)}	I _C = 25 A	T _i = 25 °C		1.85	2.10	V		
OL(Gat)	V _{GE} = 15 V	T _i = 150 °C		2.25	2.45	V		
\/	chiplevel	1 -				ļ <u> </u>		
V _{CE0}	chiplevel	$T_j = 25 ^{\circ}\text{C}$ $T_i = 150 ^{\circ}\text{C}$		0.80	0.90	V		
	V 45.V	$T_i = 150^{\circ} \text{C}$		0.70 42	0.80 48	-		
r _{CE}	V _{GE} = 15 V chiplevel	T _i = 150 °C		62	66	mΩ mΩ		
V _{GE(th)}	$V_{GE} = V_{CE}$, $I_C = 1$ m	1 '	5.3	5.8	6.3	V		
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = 12$		3.0	3.0	1	mA		
C _{ies}	VGE - O V, VCE - 12	f = 1 MHz		1.45	'	nF		
C _{oes}	$V_{CE} = 25 \text{ V}$	f = 1 MHz		0.12		nF		
C _{res}	$V_{GE} = 0 V$	f = 1 MHz		0.05		nF		
Q _G	V _{GE} = - 8 V+ 15 V			142		nC		
R _{Gint}	T _i = 25 °C			0		Ω		
t _{d(on)}	V _{CC} = 600 V	T _i = 150 °C		28		ns		
t _r	I _C = 25 A	T _i = 150 °C		40		ns		
E _{on}	$R_{G \text{ on}} = 24 \Omega$	T _i = 150 °C		2.65		mJ		
t _{d(off)}	$R_{G \text{ off}} = 24 \Omega$	T _i = 150 °C		295		ns		
t _f	_	T _i = 150 °C		68		ns		
E _{off}	V _{GE} = +15/-15 V	T _j = 150 °C		2.3		mJ		
R _{th(j-s)}	per IGBT, λ _{paste} =0.	 8 W/(mK)		1.2				
R _{th(j-s)}	per IGBT, λ _{paste} =2.	5 W/(mK)		1		K/W		
Inverse -	Diode							
$V_F = V_{EC}$	I _F = 25 A	T _j = 25 °C		2.41	2.74	V		
	V _{GE} = 0 V chiplevel	T _i = 150 °C		2.45	2.79	V		
V _{F0}		T _i = 25 °C		1.30	1.50	V		
-10	chiplevel	T _i = 150 °C		0.90	1.10	V		
r _F		T _i = 25 °C		44	50	mΩ		
	chiplevel	T _i = 150 °C		62	68	mΩ		
I _{RRM}	I _F = 25 A	T _j = 150 °C		24		Α		
Q _{rr}	di/dt _{off} = 850 A/μs	T _i = 150 °C		3.7		μС		
E _{rr}	$V_{GE} = -15 \text{ V}$	T _i = 150 °C		1.6		mJ		
R _{th(j-s)}	$V_{CC} = 600 \text{ V}$ per Diode, $\lambda_{paste} = 0$	1 1		1.52		K/W		
R _{th(j-s)}	per Diode, $\lambda_{paste}=0$			1.29		K/W		
	eling - Diode			1.20		1077		
V _F = V _{EC}	I _F = 25 A	T _i = 25 °C		2.41	2.74	V		
A E — A EC	$V_{GE} = 0 V$				2.74			
	chiplevel	T _j = 150 °C		2.45	2.79	V		
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V		
		T _j = 150 °C		0.90	1.10	V		
r _F	- chiplevel	T _j = 25 °C		44	50	mΩ		
		T _j = 150 °C		62	68	mΩ		
I _{RRM}	I _F = 25 A	T _j = 150 °C		24		Α		
Q _{rr}	$di/dt_{off} = 850 \text{ A/}\mu\text{s}$ $V_{GE} = -15 \text{ V}$	T _j = 150 °C		3.7		μC		
E_{rr}	$V_{CC} = 600 \text{ V}$	T _j = 150 °C		1.6		mJ		
R _{th(j-s)}	per Diode, λ _{paste} =0		1.52		K/W			
' 'tn(J-s)								



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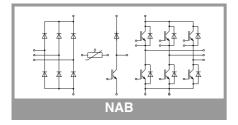
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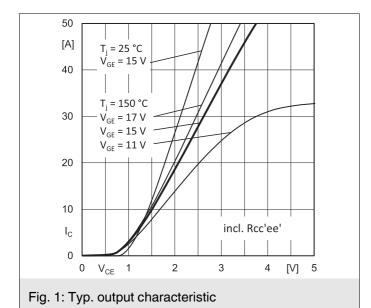
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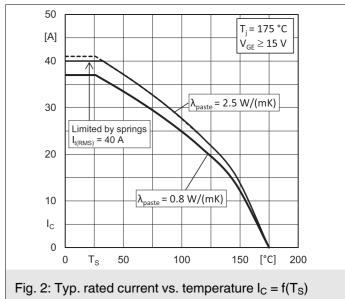
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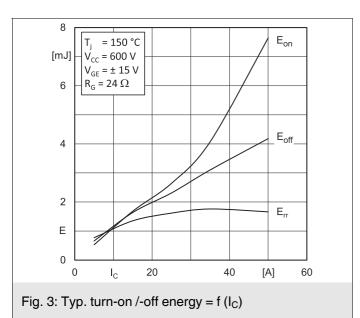
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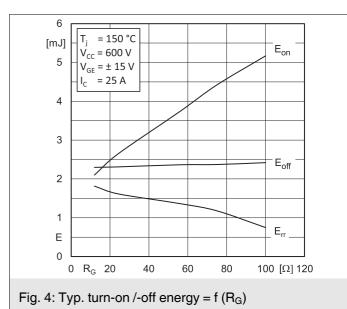
Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
Rectifier -	Diode				•			
$V_F = V_{EC}$	I _F = 13 A	T _j = 25 °C		1.00	1.21	V		
	chiplevel	T _j = 125 °C		0.90	1.10	V		
V_{F0}	chiplevel	T _j = 25 °C		0.88	0.98	V		
	Chipievei	T _j = 125 °C		0.73	0.83	V		
r _F	chiplevel	T _j = 25 °C		9.2	18	mΩ		
	Chipievei	T _j = 125 °C		13	21	mΩ		
I _R	$T_j = 145 ^{\circ}\text{C}, V_{RRM}$				1.1	mA		
R _{th(j-s)}	per Diode, λ _{paste} =0		1.25		K/W			
R _{th(j-s)}	per Diode, λ _{paste} =2		1.06		K/W			
Module								
Ms	to heat sink		2		2.5	Nm		
w				55		g		
L _{CE}			-		nΗ			
Temperature Sensor								
R ₁₀₀	T _r =100°C (R ₂₅ =10		1670 ± 3%		Ω			
R _(T)	$R_{(T)}$ =1000 Ω [1+A(7), A = 7.635*10 ⁻³ °C B = 1.731*10 ⁻⁵ °C ⁻²	T-25°C)+B(T-25°C) ²]						

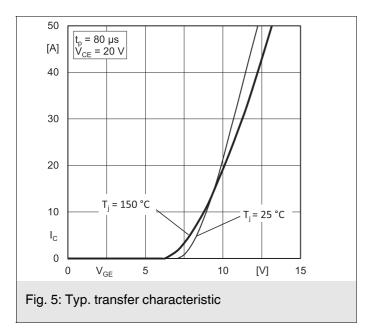


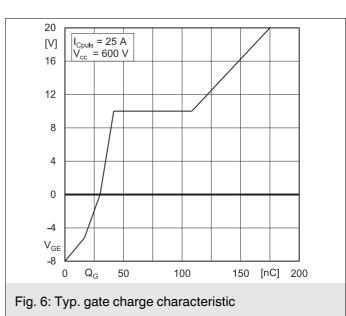


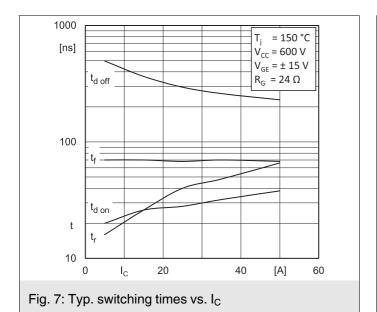


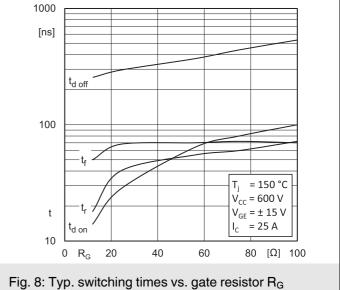


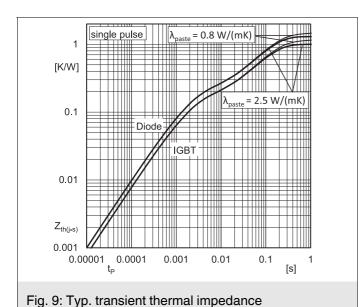


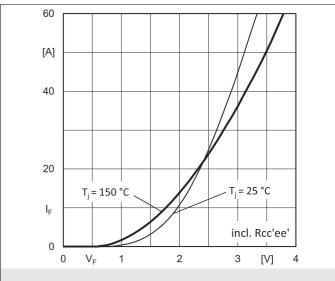


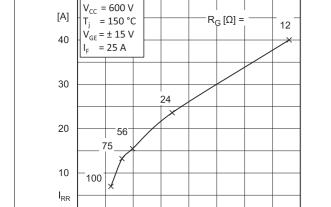






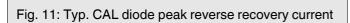






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Fig. 10: Typ. CAL diode forward characteristic



1000

1500

[A/µs]

2000

500

di_F/dt

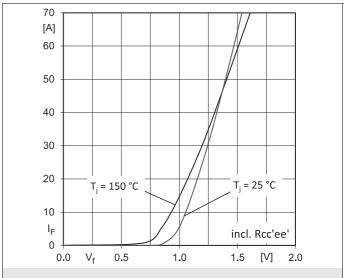
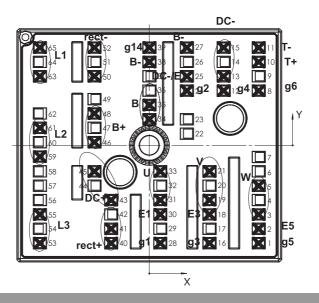


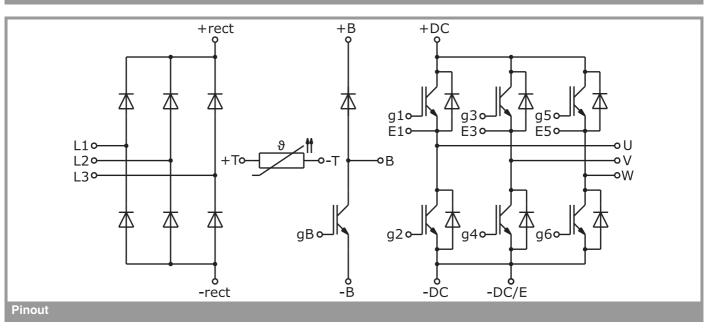
Fig. 12: Typ. input bridge forward characteristic

	Pin out										
Pin	X	Υ	Function	Pin	X	Υ	Function	Pin	X	Υ	Function
1	24,38	-21,80		23	8,38			45	-12,23		DC+
2	24,38	-18,60	E5	24	8,38	12,20	g2	46	-12,23	0,70	B+
3	24,38	-15,40	W	25	8,38	15,40	DC-/E	47	-12,23	3,90	
4	24,38	-12,20		26	8,38	18,60		48	-12,23	7,10	B+
5	24,38	-9,00	W	27	8,38	21,80	B-	49	-12,23	10,30	
6	24,38	-5,80		28	2,46	-21,80	g1	50	-12,23	15,40	rect-
7	24,38	-2,60		29	2,46	-18,60		51	-12,23	18,60	
8	24,38	12,20	g6	30	2,46	-15,40	E1	52	-12,23	21,80	rect-
9	24,38	15,40		31	2,46	-12,20	U	53	-24,38	-21,80	L3
10	24,38	18,60	T+	32	2,46	-9,00		54	-24,38	-18,60	
11	24,38	21,80	T-	33	2,46	-5,80	U	55	-24,38	-15,40	L3
12	16,58	12,20	g4	34	0,03	5,80	В	56	-24,38	-12,20	
13	16,58	15,40	DC-	35	0,03	9,00	В	57	-24,38	-9,00	
14	16,58	18,60		36	0,03	12,20		58	-24,38	-5,80	
15	16,58	21,80	DC-	37	0,03	15,40		59	-24,38	-2,50	L2
16	13,42	-21,80	g3	38	0,03	18,60	B-	60	-24,38	0,70	
17	13,42	-18,60		39	0,03	21,80	g14	61	-24,38	3,90	L2
18	13,42	-15,40	E3	40	-8,51	-21,80	rect+	62	-24,38	7,10	
19	13,42	-12,20	V	41	-8,51	-18,60	rect+	63	-24,38	15,40	L1
20	13,42	-9,00		42	-8,51	-15,40		64	-24,38	18,60	
21	13,42	-5,80	V	43	-8,51	-12,20	DC+	65	-24,38	21,80	L1
22	8,38	2,60		44	-12,23	-9,00					

all values in mm



Pinout and Dimensions



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

*IMPORTANT INFORMATION AND WARNINGS

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